



ACE9060M

N-Channel 60-V MOSFET

Description

ACE9060M uses advanced trench technology to provide excellent $R_{DS(ON)}$.

This device particularly suits for low voltage application such as power management of desktop computer or notebook computer power management, DC/DC converter.

Features

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Applications:

- Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	90	A
$T_C=25^\circ\text{C}$			
Pulsed Drain Current ^b	I_{DM}	240	A
Continuous Source Current (Diode Conduction) ^a	I_S	90	A
Power Dissipation ^a	P_D	300	W
$T_C=25^\circ\text{C}$			
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Unit
Maximum Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	1	

Notes

A. Package Limited.

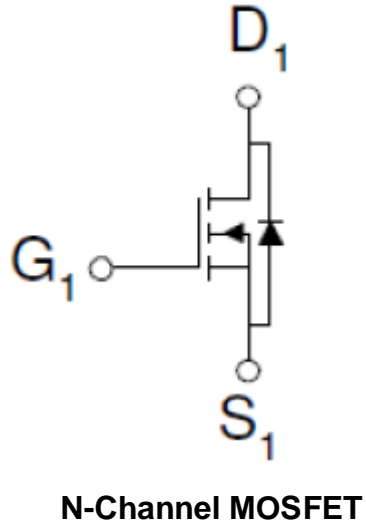
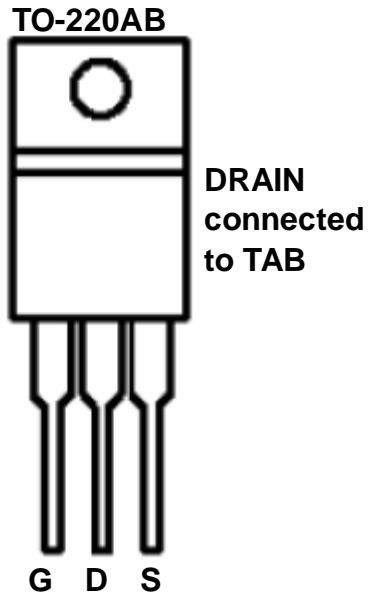
B. Pulse width limited by maximum junction temperature



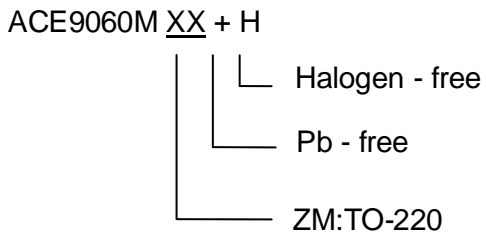
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Packaging Type



Ordering information





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Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	110			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$			26.5	m Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			32.5	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$		23		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 55 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		19		nC
Gate-Source Charge	Q_{gs}			5.4		
Gate-Drain Charge	Q_{gd}			9.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30 \text{ V}, R_L = 1.5 \Omega, I_D = 20 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		11		ns
Rise Time	t_r			16		
Turn-Off Delay Time	$t_{d(off)}$			66		
Fall Time	t_f			18		
Input Capacitance	C_{iss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		2263		pF
Output Capacitance	C_{oss}			196		
Reverse Transfer Capacitance	C_{rss}			162		

Note:

a. Pulse test: $PW \leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.

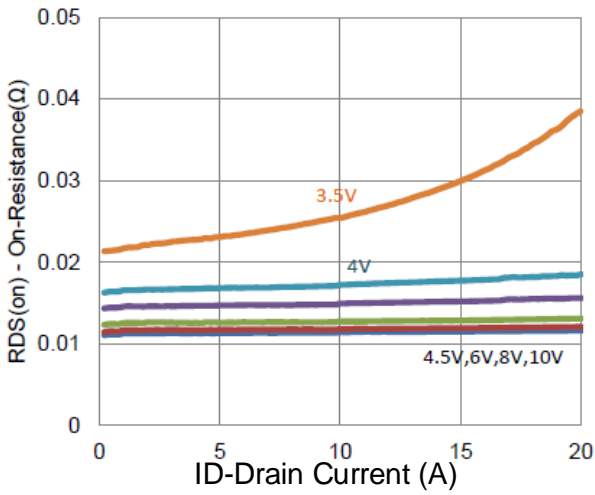
b. Guaranteed by design, not subject to production testing.



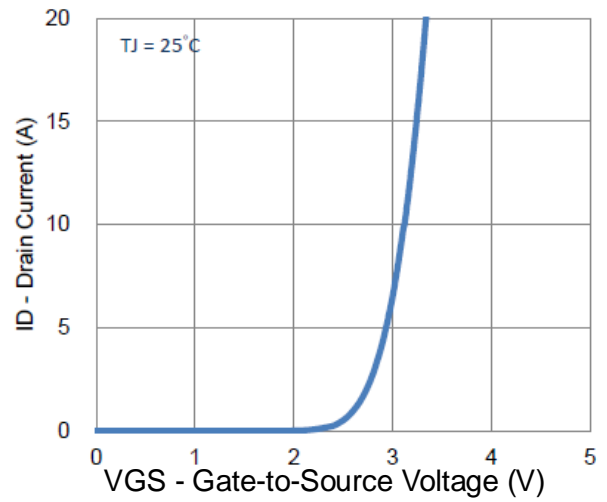
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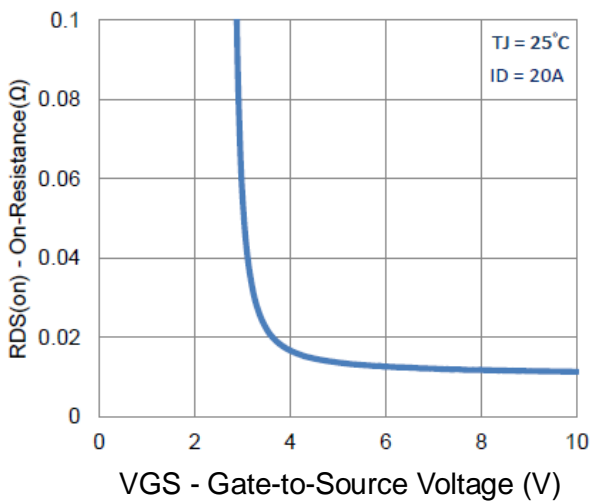
Typical Performance Characteristics (N-Channel)



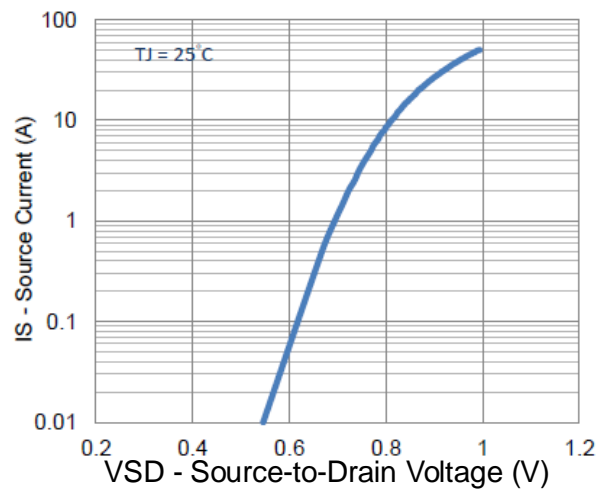
1. On-Resistance vs. Drain Current



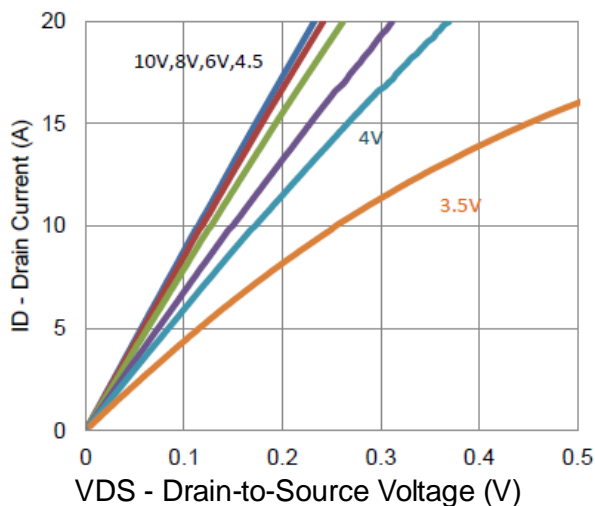
2. Transfer Characteristics



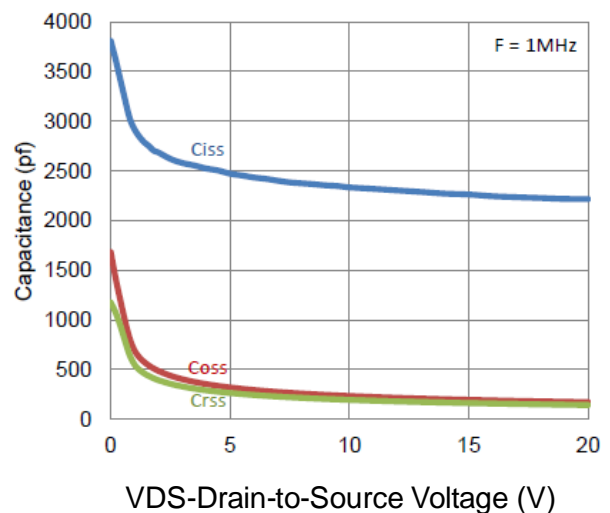
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics



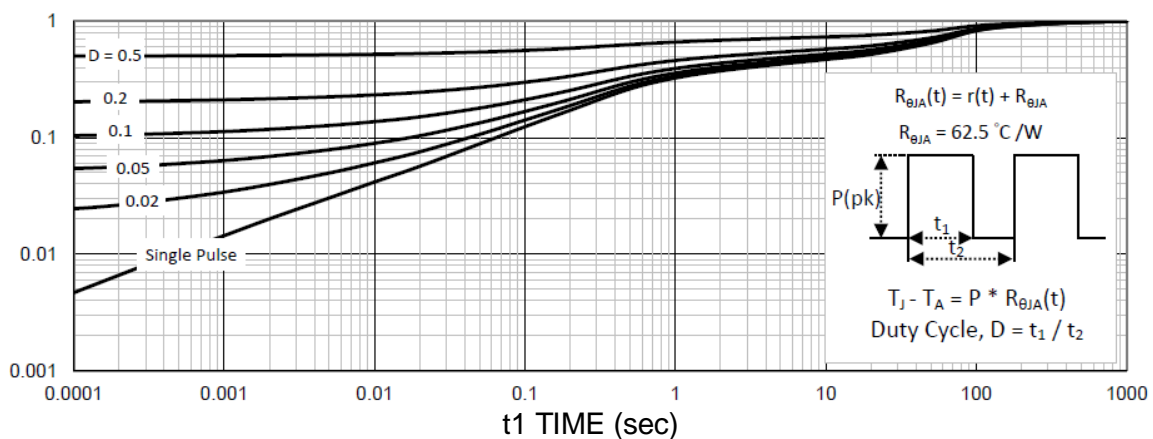
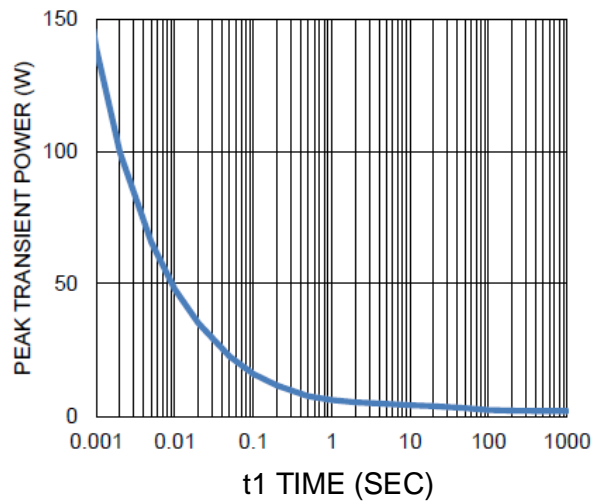
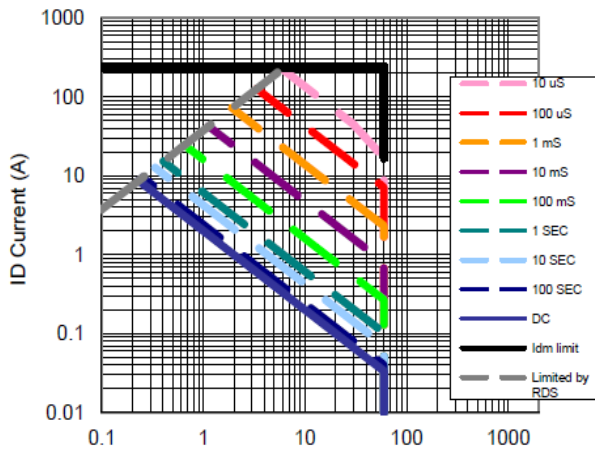
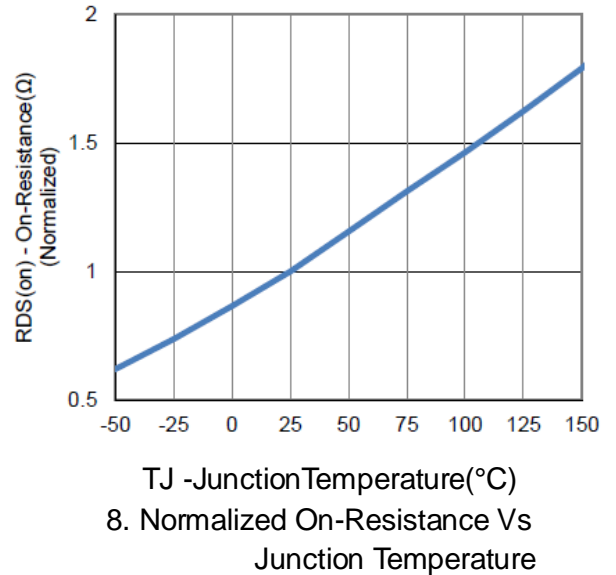
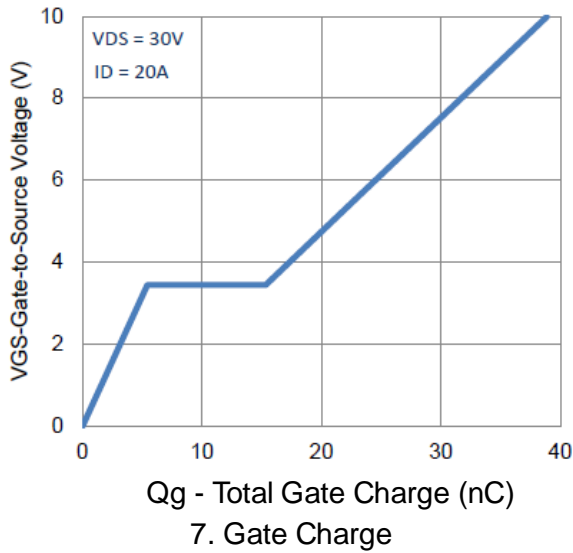
6. Capacitance



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Typical Performance Characteristics



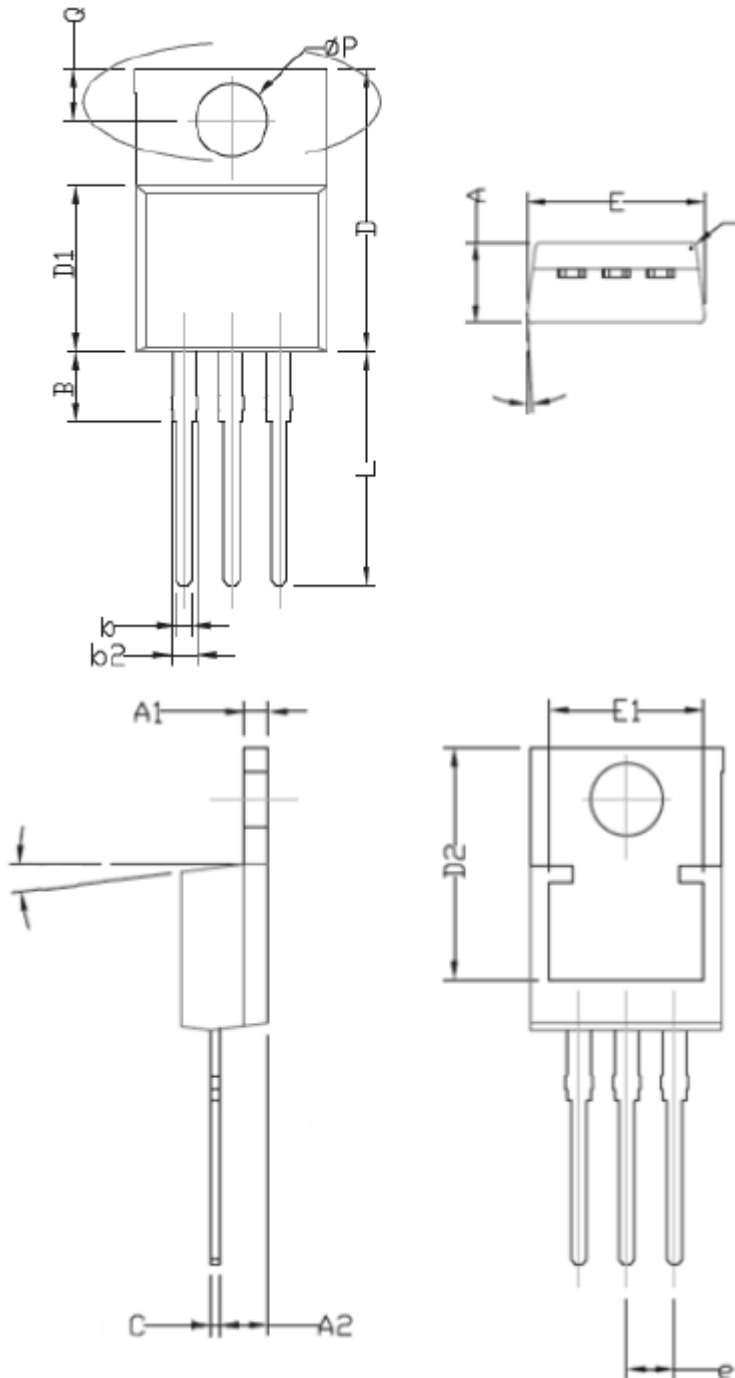


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Packing Information

TO-220AB



DIM.	MILLIMETERS	
	MIN	MAX
A	4.24	4.72
A1	1.11	1.41
A2	2.22	2.7
B	2.6	3.9
b	0.66	0.94
b2	1.17	1.45
c	0.4	0.6
D	14.5	15.74
D1	8.4	9.65
D2	12.08	12.48
E	9.7	10.54
E1	8	8.4
e	2.49	2.59
L	12.27	14.5
ØP	3.55	3.89
Q	2.58	2.98



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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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